Central™
Semiconductor Corp.

PROCESS CPD18

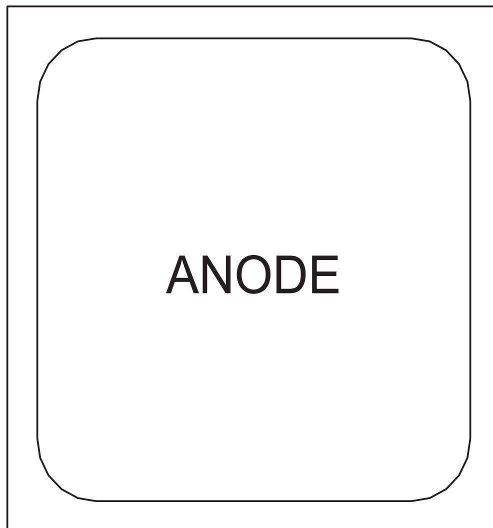
Ultra Fast Rectifier

8 Amp Glass Passivated Rectifier Chip

PROCESS DETAILS

Process	GLASS PASSIVATED MESA
Die Size	98 x 98 MILS
Die Thickness	12.2 MILS
Anode Bonding Pad Area	82.5 x 82.5 MILS
Top Side Metalization	Au - 5,000Å
Back Side Metalization	Au - 2,000Å

GEOMETRY



BACKSIDE CATHODE

R0

GROSS DIE PER 4 INCH WAFER
1,170

PRINCIPAL DEVICE TYPES
1N5807 thru 1N5811
UES1301 thru UES1306
UES1401 thru UES1403
CUDD8-02 Series

The Typical Electrical Characteristics data for this chip is currently being revised.

For the latest updated data for this Chip Process, please visit our website at:

www.centralsemi.com/chip

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